



**1N483B thru  
1N486B and  
1N5194 thru  
1N5196**

SANTA ANA, CA  
For more information call:  
(714) 979-8220

**FEATURES**

- Voidless hermetically sealed glass package (D0-35).
- Triple layer passivation.
- Metallurgically bonded.
- TX types available per MIL-S-19500/118C.
- 1N5194 thru 1N5196 only available in surface mount.

**MAXIMUM RATINGS**

Operating Temperature: -65°C to +200°C.  
Storage Temperature: -65°C to +200°C.  
Surge Current: 2A

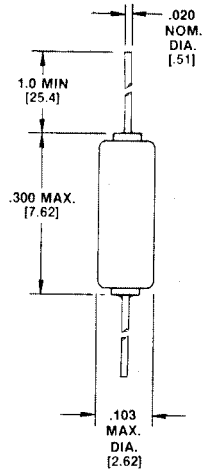
**ELECTRICAL CHARACTERISTICS**

TYPE	WORKING PEAK REVERSE VOLTAGE V <sub>RWM</sub>	BREAKDOWN VOLTAGE (MIN.) V <sub>(BR)</sub> @ 100 µA	AVERAGE RECTIFIED CURRENT I <sub>O</sub>		FORWARD VOLTAGE DROP (MAX.) V <sub>F</sub>	REVERSE CURRENT (MAX.) I <sub>R</sub> @ V <sub>RWM</sub>		SURGE CURRENT (MAX.) (NOTE 1) I <sub>S</sub> SURGE	JUNCTION CAPACITANCE C <sub>J</sub> @ 0V
			AMPS			µA			
			25°C	150°C		25°C	150°C		
JAN 1N483B	70	80	.2	.05	1.0V (pk) @ 100mA pulse	.025	5	2	8
JAN 1N485B	180	200	.2	.05		.025	5	2	8
JAN 1N486B	225	250	.2	.05		.025	5	2	8
JAN 1N5194 JAN 1N5195 JAN 1N5196	SAME AS JAN 1N483B SAME AS JAN 1N485B SAME AS JAN 1N486B				} EXCEPT: PACKAGE D035				

PACKAGE: D07 for JAN 1N483B, 485B, 486B.  
D035 for JAN 1N5194, JAN 1N5195, and JAN 1N5196.

NOTE 1: I<sub>O</sub> = 200mAdc, 10 - 8.3msec surges

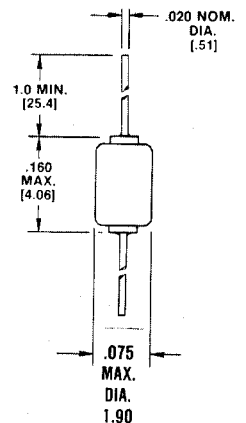
**GENERAL PURPOSE  
SILICON DIODES**



**FIGURE 1A  
PACKAGE D07**

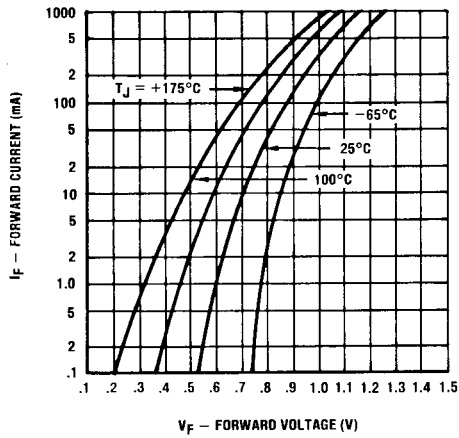
**MECHANICAL  
CHARACTERISTICS**

Case: Hermetically sealed glass case.  
Lead Material: Tinned copper.  
Marking: Body painted, alpha numeric.  
Polarity: Cathode band.

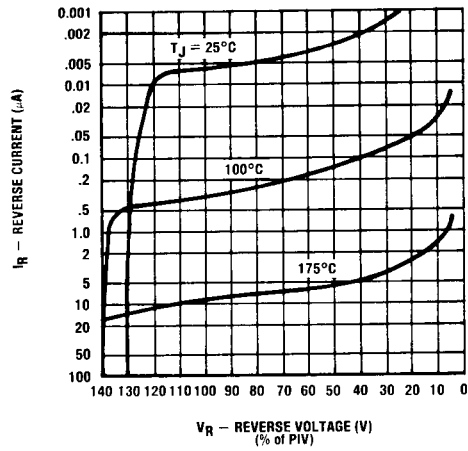


**FIGURE 1B  
PACKAGE D0-35**

# 1N483B - 1N486B. 1N5194 - 1N5196



**FIGURE 2**  
FORWARD VOLTAGE vs. FORWARD CURRENT



**FIGURE 3**  
REVERSE VOLTAGE vs. REVERSE CURRENT